

# LZ2354J

1/3 type B/W CCD Area Sensor for EIA

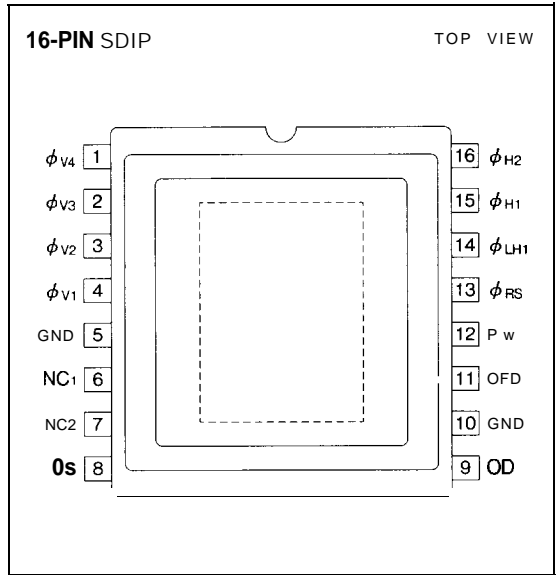
## DESCRIPTION

LZ2354J is a 1/3-type (6.0 mm) solid-state image sensor that consists of PN photo-diodes and CCDS (charge-coupled devices). Having approximately 410000 pixels (horizontal 811 × vertical 507), the sensor provides a high resolution stable B/W image.

## FEATURES

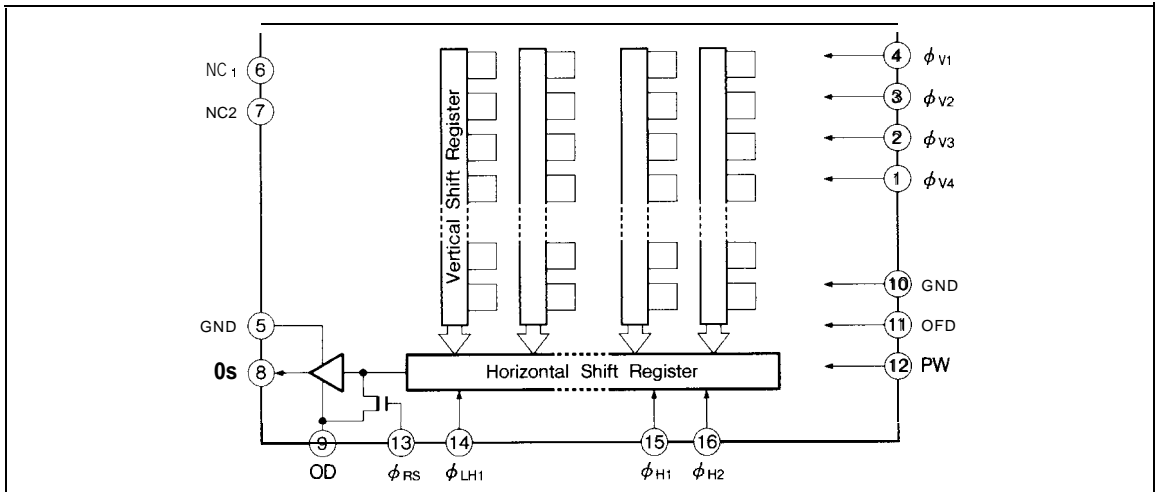
- Number of pixels : 768 (H) × 494 (V)  
Pixel pitch : 6.4 μm (H) × 7.5 μm (V)  
Number of optical black pixels : Horizontal; front 3 and rear 40  
Vertical; front 11 and rear 2
- Low fixed pattern noise and lag
- No burn-in and no image distortion
- Blooming suppression structure
- Built-in output amplifier
- Variable electronic shutter (1/60 to 1/1 000 s)
- Compatible with EIA standard
- Package : 16-pin SDIP [CERDIP] (WDIP01 6-N-0450)

## PIN CONNECTIONS



2 CCD AREA SENSORS

## BLOCK DIAGRAM



## PIN DESCRIPTION

SYMBOL	PIN NAME
OD	Output transistor drain
Os	Video output
$\phi_{RS}$	Reset transistor clock
$\phi_{V1}, \phi_{V2}, \phi_{V3}, \phi_{V4}$	Vertical shift register clock
$\phi_{H1}, \phi_{H2}$	Horizontal shift register clock
$\phi_{LH1}$	Horizontal shift register final stage clock
OFD	Overflow drain
PW	P type well
GND	Ground
NC <sub>1</sub> , NC <sub>2</sub>	No connection

## ABSOLUTE MAXIMUM RATINGS

(Ta = 25°C)

PARAMETER	SYMBOL	RATING	UNIT	NOTE
Output transistor drain voltage	V <sub>oo</sub>	0 to +18	V	
Reset transistor clock voltage	V $\phi_{RS}$	V <sub>PW</sub> to +12	v	
Vertical shift register clock voltage	V $\phi_V$	V <sub>PW</sub> to +18	v	
Horizontal shift register clock voltage	V $\phi_H$	V <sub>PW</sub> to +8	v	
Horizontal shift register final stage clock voltage	V $\phi_{LH}$	V <sub>PW</sub> to +8	v	
Overflow drain voltage	V <sub>OFD</sub>	0 to +55	v	
Voltage difference between PW and vertical clock	V <sub>PW</sub> - V $\phi_V$	-28 to 0	v	1
Storage temperature	T <sub>stg</sub>	-20 to +80	°C	
Operating ambient temperature	T <sub>opr</sub>	-20 to +70	°C	

## NOTE :

1. The OFD clock  $\phi_{OFD}$  is excluded

## RECOMMENDED OPERATING CONDITIONS

PARAMETER		SYMBOL	MIN.	TYP.	MAX.	UNIT	NOTE
Operating ambient temperature		Topr		25.0		°C	
Output transistor drain voltage		VOD	14.5	15.0	16.0	v	
Overflow drain voltage	When DC is applied	Vom	5.0		19.0	v	1
	When pulse is applied p-p level	V $\phi$ OFD	23.0			v	2
Ground		GND		0.0		v	
P-well voltage		VFW	- 10.0		V $\phi$ VL	v	
Vertical shift register clock	LOW level	V $\phi$ V1L, V $\phi$ V3L V $\phi$ V2L, V $\phi$ V4L	-9.5	- 9.0	-8.5	v	
	INTERMEDIATE level	V $\phi$ V1I, V $\phi$ V3I V $\phi$ V2I, V $\phi$ V4I		0.0		v	
	HIGH level	V $\phi$ V1H, V $\phi$ V3H	16.0	16.5	17.0	v	
Horizontal shift register clock	LOW level	V $\phi$ H1L, V $\phi$ H2L	- 0.05	0.0	0.05	v	
	HIGH level	V $\phi$ H1H, V $\phi$ H2H	4.7	5.0	6.0	v	
Horizontal shift register final stage clock	LOW level	V $\phi$ LH1L	- 0.05	0.0	0.05	v	
	HIGH level	V $\phi$ LH1H	4.7	5.0	6.0	v	
Reset gate clock	LOW level	V $\phi$ RSL	0.0		V <sub>OD</sub> -11.0	v	
	HIGH level	V $\phi$ RSH	V <sub>OD</sub> -6.5		10.0	v	
Vertical shift register clock frequency		f $\phi$ V1, f $\phi$ V2 f $\phi$ V3, f $\phi$ V4		15.73		kHz	
Horizontal shift register clock frequency		f $\phi$ H1, f $\phi$ H2 f $\phi$ LH1		14.32		MHz	
Reset gate clock frequency		f $\phi$ RS		14.32		MHz	

\* Connect NC 1 and NC2 to GND directly or through a capacitor larger than 0.047  $\mu$ F.

## NOTES :

1. When DC voltage is applied, shutter speed is 1/M seconds.
2. When pulse is applied, shutter speed is less than 1/W seconds

## ELECTRICAL CHARACTERISTICS (Drive method : Field Accumulation)

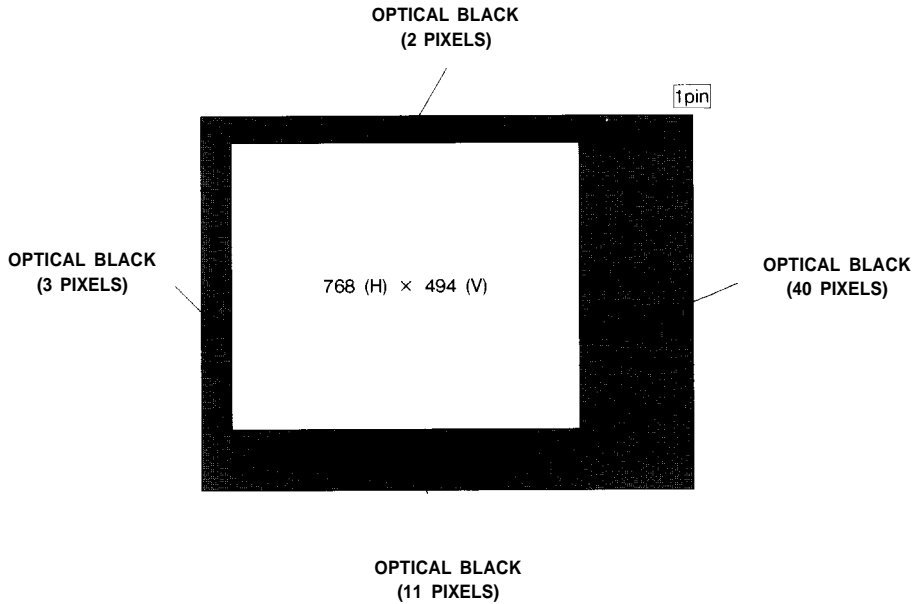
( $T_a=25^{\circ}\text{C}$ , Operating conditions : typical values for the recommended operating conditions, Color temperature of light source : 3200 K / IR cut-off filter (CM-500, 1 mmt))

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	NOTE
Standard output voltage	$V_o$		150		mV	2
Photo response non-uniformity	PRNU			10	%	3, 4
Saturation output voltage	vast	700			mV	3, 5
Dark output voltage	$V_{\text{dark}}$		0,5	3.0	mV	1, 6
Dark signal non-uniformity	DSNU		0.5	2.0	mV	1, 3, 7
Sensitivity	R	300	400		mV	8
Gamma	$\gamma$		1			
Smear ratio	SMR		- 75	- 70	dB	9, 10
Image lag	AI			1.0	0/0	11
Blooming suppression ratio	ABL	1 000				9, 12
Output transistor drain current	$I_{\text{OD}}$		4.0	8.0	mA	
Output impedance	$R_o$		350		$\Omega$	
Dark noise	$V_{\text{noise}}$		0.2	0.3	mV	13
OB difference in level				1.0	mV	1, 14

## NOTES :

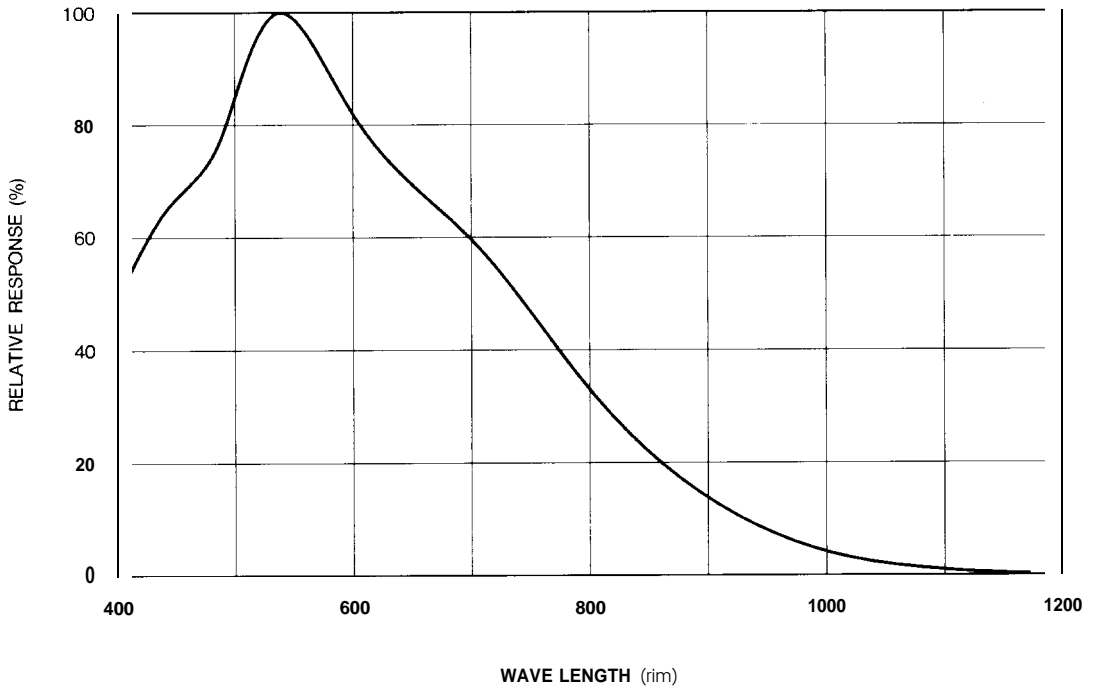
- $T_a : +60^{\circ}\text{C}$
- The average output voltage under the uniform illumination. The standard exposure condition is defined when  $V_o$  is 150 mV.
- The image area is divided into 10X 10 segments. The segment's voltage is the average output voltage of all the pixels within the segment.
- PRNU is defined by  $(V_{\text{max}} - V_{\text{min}})/V_o$ , where  $V_{\text{max}}$  and  $V_{\text{min}}$  are the maximum and the minimum values of each segment's voltage respectively, under the standard exposure condition.
- The minimum segment's voltage under 10 times exposure of the standard exposure condition.
- The average output voltage under the non-exposure condition.
- DSNU is defined by  $(V_{\text{dmax}} - V_{\text{dmin}})$ , where  $V_{\text{dmax}}$  and  $V_{\text{dmin}}$  are the maximum and the minimum values of each segment's voltage respectively, under the non-exposure condition.
- The average output voltage when a 1000 lux light source with a 90% reflector is imaged with a lens at F4, f50 mm.
- The sensor is exposed only in the central area of  $V/I$  O square, where V is the vertical image size.
- SMR is defined by the ratio of the smear voltage detected during the vertical blanking period to the maximum output voltage in the  $V/I$  O square, with a lens at F4.
- f. The sensor is exposed at the exposure level corresponding to the standard condition. AI is defined by the ratio of the lag voltage measured at the 1st field during the non-exposure period to the standard output voltage.
- ABL is defined by the ratio of the exposure at the standard condition to the exposure at a point where a blooming is observed.
- The RMS value of the dark noise after CDS, The bandwidth range is from 100 kHz to 4.2 MHz. SC trap on.
- The difference of the average output voltage between the effective area and the OB area under the non-exposure condition.

PIXEL STRUCTURE



CCD REA N ORS  
**2**

SPECTRAL RESPONSE EXAMPLE

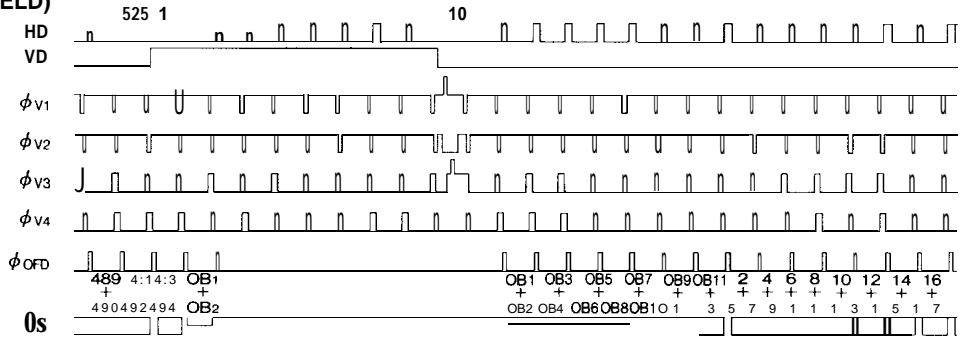


TIMING DIAGRAM EXAMPLE

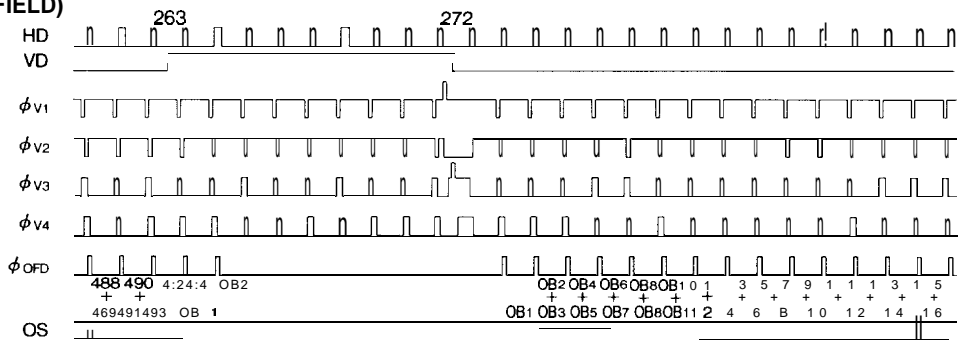
VERTICAL TRANSFER TIMING

Shutter speed  
1/2000 s

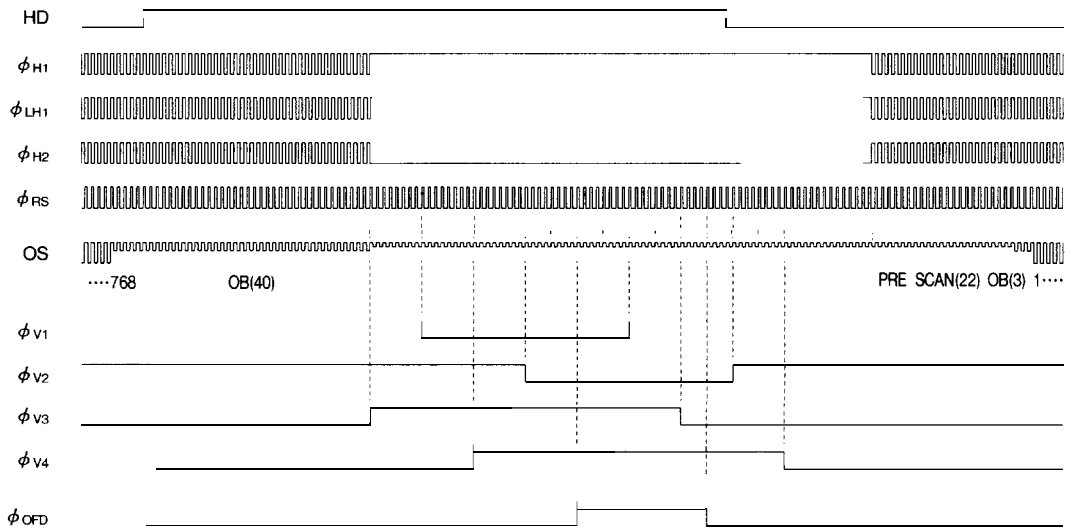
(ODD FIELD)



(EVEN FIELD)

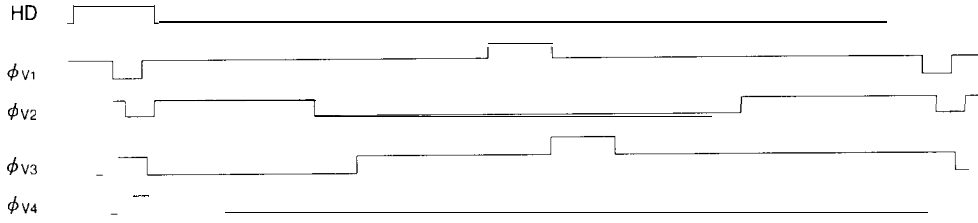


HORIZONTAL TRANSFER TIMING

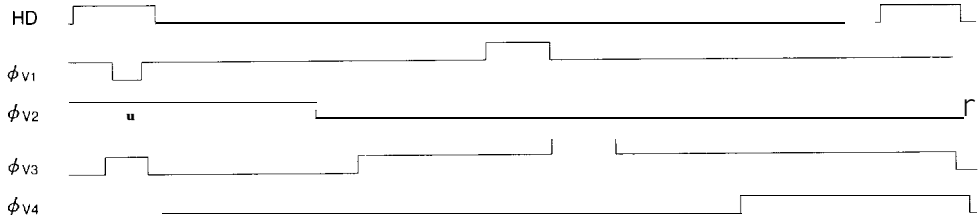


## READOUT TIMING

## (ODD FIELD)



## (EVEN FIELD)



SYSTEM CONFIGURATION EXAMPLE

